

HG

1N914 THRU 1N4454 SMALL SIGNAL SWITCHING DIODE

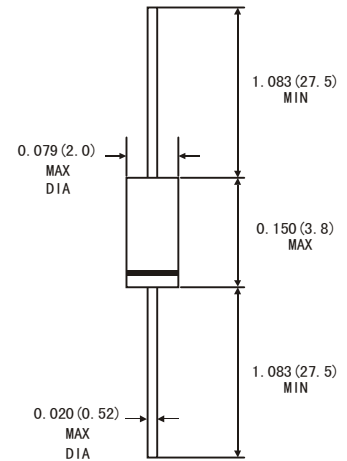
FEATURES

- Silicon epitaxial planar diode
- Fast switching diodes
- 1N4149, 1N4447, 1N4449 are also available in glass case DO-34

MECHANICAL DATA

- Case: DO-35 glass case
- Polarity: Color band denotes cathode end
- Weight: Approx. 0.13gram

DO-35



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Type	Peak reverse voltage V _{RM} (V)	Max. Aver. Rectified Current I(AV)mA	Max. Power Dissip At 25°C P _{tot} (mW)	Max. Junction Temperature T _J (°C)	Max. Forward Voltage drop		Max. Reverse Current		Max. Reverse Recovery Time	
					V _F (V)	at I _F (mA)	I _R (nA)	at V _R (V)	I _{rr} (ns) Max.	Test conditions
1N914	100	75	500	200	1.0	10	25	20	4.0	I _F = 10mA, V _R = 6V, R _L = 100Ω, to I _R = 1 mA
1N4149 ¹⁾	100	150	500	200	1.0	10	25	20	4.0	I _F = 10mA, V _R = 6V, R _L = 100Ω, to I _R = 1 mA
1N4150	50	200	500	200	1.0	200	100	50	4.0	I _F = I _R = 10 to 200mA, to 0.1 I _F
1N4152	40	150	400	175	0.55	0.10	50	30	2.0	I _F = 10mA, V _R = 6V, R _L = 100Ω, to I _R = 1 mA
1N4153	75	150	400	175	0.55	0.10	50	50	2.0	I _F = 10mA, V _R = 6V, R _L = 100Ω, to I _R = 1 mA
1N4154	35	150 ²⁾	500	200	1.0	0.10	100	25	2.0	I _F = 10mA, V _R = 6V, R _L = 100Ω, to I _R = 1 mA
1N4447 ¹⁾	100	150	500	200	1.0	20	25	20	4.0	I _F = 10mA, V _R = 6V, R _L = 100Ω, to I _R = 1 mA
1N4449 ¹⁾	100	150	500	200	1.0	30	25	20	4.0	I _F = 10mA, V _R = 6V, R _L = 100Ω, to I _R = 1 mA
1N4450	40	150	400	175	0.54	0.50	50	30	4.0	I _F = I _R = 10mA to, I _R = 1mA
1N4451	40	150	400	175	0.50	0.10	50	30	10	I _F = I _R = 10mA to, I _R = 1mA
1N4453	30	150	400	175	0.55	0.01	50	20		
1N4454	75	150	400	175	1.0	10	100	50	4.0	I _F = I _R = 10mA to, I _R = 1mA

Notes: 1. These diodes are also available in glass case DO-34

2. Valid provided that leads at a distance of 8mm from case are kept at ambient temperature parameters for diodes in case DO-34: P_{tot} = 300mW T_{STG} = -65 to +175°C T_J = 175°C R_{θJA} = 400K/W